

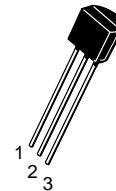
High Voltage Transistors

PNP Silicon

BF423

MAXIMUM RATINGS

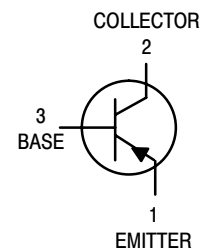
Rating	Symbol	BF423	Unit
Collector–Emitter Voltage	V_{CEO}	–250	Vdc
Collector–Base Voltage	V_{CBO}	–250	Vdc
Emitter–Base Voltage	V_{EBO}	–5.0	Vdc
Collector Current — Continuous	I_C	–500	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$



CASE 29–11, STYLE 14
TO–92 (TO–226AA)

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (1) ($I_C = -1.0 \text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	–250	—	Vdc
Collector–Base Breakdown Voltage ($I_C = -100 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	–250	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = -100 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	–5.0	—	Vdc
Collector Cutoff Current ($V_{CB} = -200 \text{ Vdc}, I_E = 0$)	I_{CBO}	—	—	μAdc
Emitter Cutoff Current ($V_{EB} = -5.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	—	nAdc

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$; Duty Cycle $\leq 2.0\%$.

BF423

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ($I_C = -25\text{ mA}$, $V_{CE} = -20\text{ Vdc}$)	h_{FE}	50	—	—
Collector–Emitter Saturation Voltage ($I_C = -20\text{ mAdc}$, $I_B = -2.0\text{ mAdc}$)	$V_{CE(\text{sat})}$	—	-0.5	Vdc
Base–Emitter Saturation Voltage ($I_C = -20\text{ mA}$, $I_B = -2.0\text{ mA}$)	$V_{BE(\text{sat})}$	—	-2.0	Vdc
SMALL–SIGNAL CHARACTERISTICS				
Current–Gain — Bandwidth Product ($I_C = -10\text{ mAdc}$, $V_{CE} = -10\text{ Vdc}$, $f = 20\text{ MHz}$)	f_T	60	—	MHz
Common Emitter Feedback Capacitance ($V_{CB} = -30\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{re}	—	2.8	pF

BF423

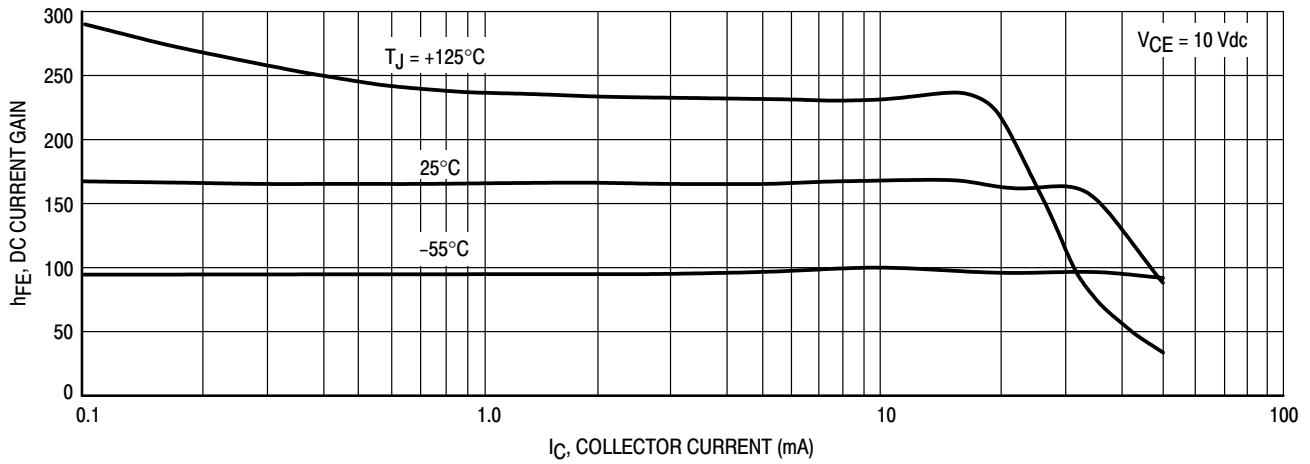


Figure 1. DC Current Gain

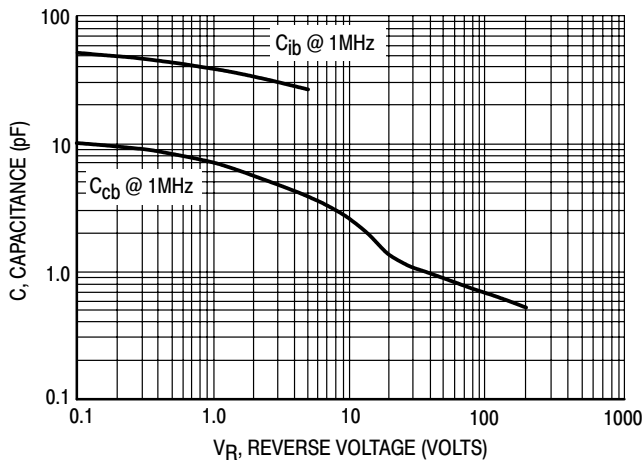


Figure 2. Capacitance

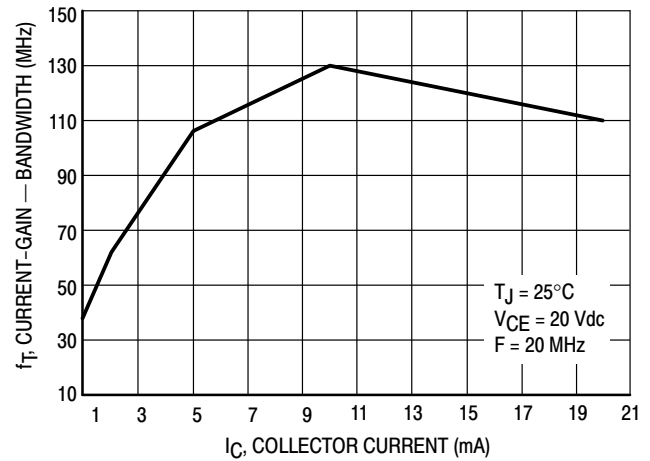


Figure 3. Current-Gain — Bandwidth

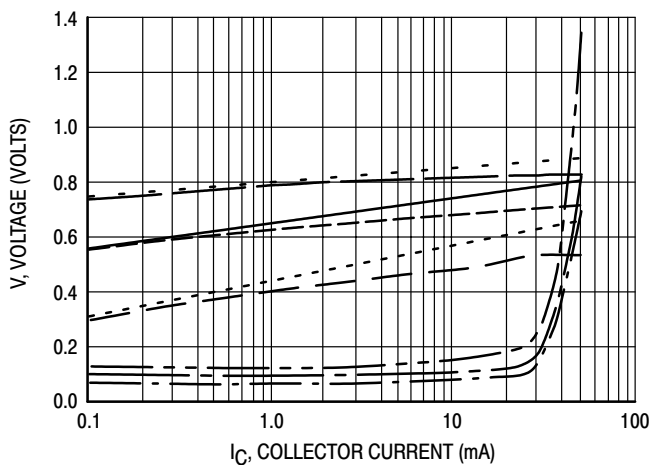


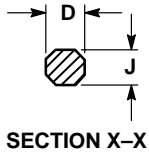
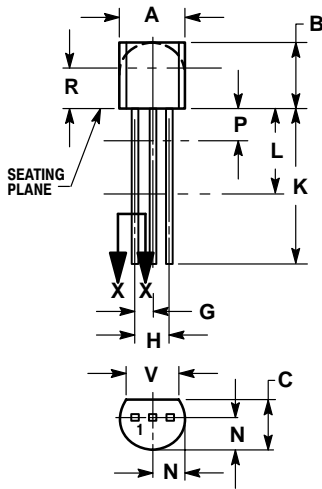
Figure 4. "ON" Voltages

- $V_{CE(sat)}$ @ 25°C , $I_C/I_B = 10$
- $V_{CE(sat)}$ @ 125°C , $I_C/I_B = 10$
- $V_{CE(sat)}$ @ -55°C , $I_C/I_B = 10$
- $V_{BE(sat)}$ @ 25°C , $I_C/I_B = 10$
- $V_{BE(sat)}$ @ 125°C , $I_C/I_B = 10$
- $V_{BE(sat)}$ @ -55°C , $I_C/I_B = 10$
- $V_{BE(on)}$ @ 25°C , $V_{CE} = 10 \text{ V}$
- $V_{BE(on)}$ @ 125°C , $V_{CE} = 10 \text{ V}$
- $V_{BE(on)}$ @ -55°C , $V_{CE} = 10 \text{ V}$

BF423

PACKAGE DIMENSIONS

CASE 029-11 (TO-226AA) ISSUE AJ




STYLE 14:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---

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